

S1376

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

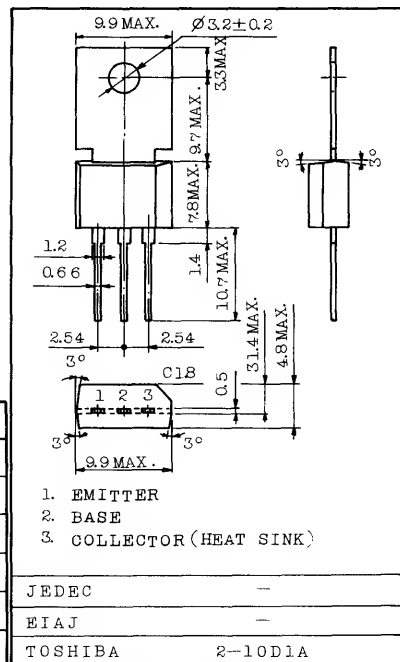
MEDIUM POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

. Complementary to S1375

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-80	V
Collector-Emitter Voltage	V_{CE0}	-80	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-750	mA
Base Current	I_B	-500	mA
Collector Power Dissipation	P_C	1.5	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 1.4g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB} = -30V, I_E = 0$	-	-	-0.5	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = -5V, I_C = 0$	-	-	-1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	80	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -150mA$	70	-	240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -500mA$	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	-	-	-0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V, I_C = -500mA$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -150mA$	50	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	20	-	pF

